Philips Semiconductors

Product specification

Rectifier diodes Schottky barrier

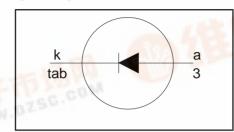
PBYR1645B series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL

WWW.DZ



QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{F(AV)} = 16 \text{ A}$
 $V_F \le 0.57 \text{ V}$

GENERAL DESCRIPTION

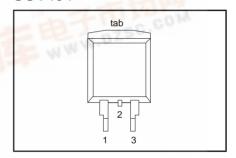
Schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1645B series is supplied in the surface mounting SOT404 package.

PINNING

PIN	DESCRIPTION		
1	no connection		
2	cathode ¹		
3	anode		
tab	cathode		

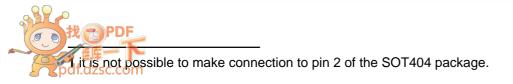
SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{RRM}	Peak repetitive reverse	PBYR16	4	40B 40	45B 45	V
V RRM V _{RWM}	voltage Working peak reverse	13 m	_	40	45	V
	voltage	T < 116 °C			45	V
V_R	Continuous reverse voltage	T _{mb} ≤ 116 °C	-	40	45	_ v
I _{F(AV)}	Average rectified forward current	square wave; $\delta = 0.5$; $T_{mb} \le 131$ °C	-	,	16	А
I _{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{mb} \le 131$ °C	-	3	32	Α
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-10		35	A
	current	t = 8.3 ms sinusoidal; T _j = 125 °C prior to surge: with reapplied V _{SSWeet}	E	O.WWW	50	A
I _{RRM}	Peak repetitive reverse surge current	surge; with reapplied V _{RRM(max)} pulse width and repetition rate limited by T _{i max}	-		1	А
T _j	Operating junction	initiod by I j max	-	1	50	°C
T _{stg}	temperature Storage temperature	SC. COM	- 65	1	75	°C



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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction		-	-	1.5	K/W
R _{th j-a}	to mounting base Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	I _F = 16 A; T _i = 125°C	-	0.53	0.57	V
	_	$I_{\rm F} = 16 {\rm A}$	-	0.55	0.63	V
I _R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	0.2	1.7	mΑ
		$V_R = V_{RWM}$; $T_i = 100$ °C	-	27	40	mΑ
C _d	Junction capacitance	$V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_j = 25 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	470	-	pF

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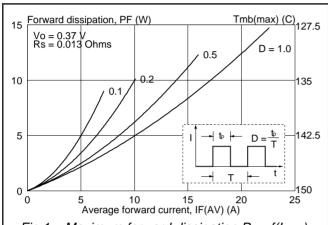


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

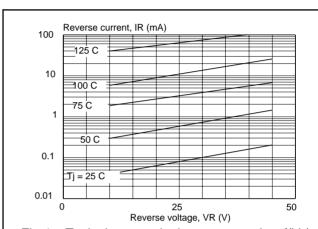


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_j

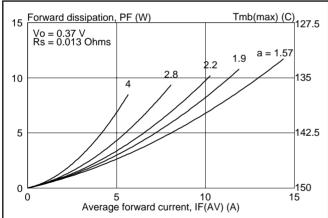


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.

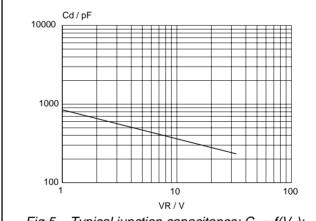


Fig.5. Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25^{\circ}\text{C}$ to 125°C .

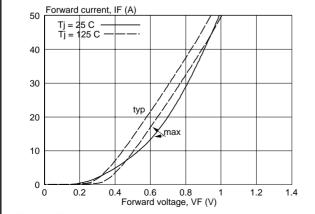


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

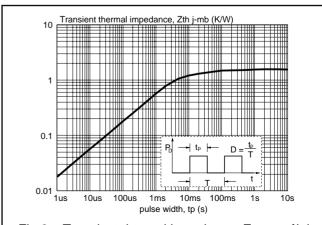
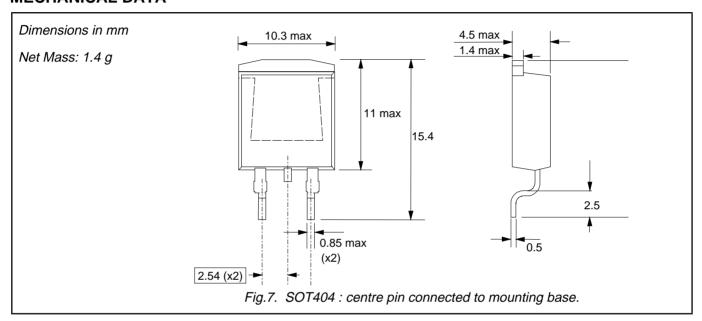


Fig.6. Transient thermal impedance; $Z_{th j-mb} = f(t_p)$.

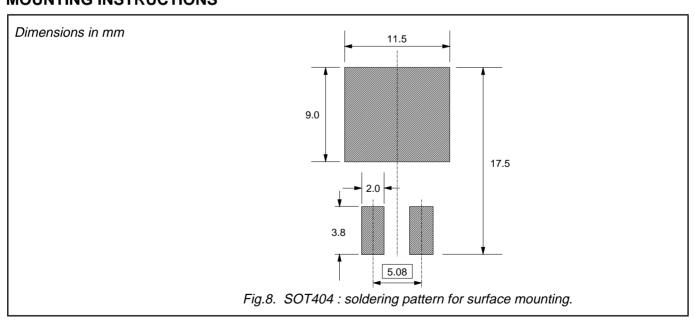
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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

- Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

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Schottky	barrier

PBYR1645B series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
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Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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